NSN 5962-01-180-4306

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-180-4306

Body Length:	
0.960 inches	
Body Width:	
Between 0.220 inches a	nd 0.310 inches
Body Height:	
0.185 inches	
Maximum Power Dissi	pation Rating:
715.0 milliwatts	
Operating Tempurature	e Range:
-55.0/+125.0 degrees ce	
Storage Tempurature I	
-65.0/+150.0 degrees ce	
Features Provided:	
Hermetically sealed and	monolithic and bipolar and programmable and high impedance and 3-state output
Inclosure Material:	
Ceramic and glass	
Inclosure Configuratio	n:
Dual-in-line	
Output Logic Form:	
Transistor-transistor logi	с
Input Circuit Pattern:	
12 input	
Case Outline Source A	nd Designator:
D-6 mil-m-38510	
Terminal Surface Treat	iment:
Solder	
Voltage Rating And Ty	pe Per Characteristic:
5.5 volts power source	
Time Rating Per Chact	eristic:
125.00 nanoseconds pr	opagation delay time, low to high level output and 125.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type:	
Rom	
Memory Capacity:	
Unknown	
Test Data Document:	
35012-102093 drawing	(this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification	on, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Qu	antity:
18 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

NSN 5962-01-180-4306

Memory Microcircuit - Page 2 of 2

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

